

1. DESCRIPTION

1.1 Features

- Current transfer ratio (CTR : MIN. 20% at $I_F = \pm 1$ mA, $V_{CE} = 5$ V)
- High input-output isolation voltage (V_{iso} = 5,000Vrms)
- Response time (tr : TYP. $4\mu s$ at $V_{CE} = 2V$, $I_C = 2mA$, $R_L = 100\Omega$)
- Dual-in-line package :

LTV-814: 1-channel type

LTV-824: 2-channel type

LTV-844: 4-channel type

■ Wide lead spacing package :

LTV-814M: 1-channel type

LTV-824M: 2-channel type

LTV-844M: 4-channel type

■ Surface mounting package :

LTV-814S: 1-channel type

LTV-824S: 2-channel type

LTV-844S: 4-channel type

■ Tape and reel packaging :

LTV-814S-TA: 1-channel type

LTV-814S-TA1 : 1-channel type

LTV-814S-TP: 1-channel type

LTV-824S-TA1: 2-channel type

■ Safety approval

UL 1577

VDE DIN EN60747-5-5 (VDE 0884-5)

CSA CA5A

Nordic Safety (FIMKO/NEMKO/SEMKO/DEMKO)

■ BSI RoHS Compliance

All materials be used in device are followed EU RoHS directive (No.2002/95/EC).

- ESD pass HBM 8000V/MM2000V
- MSL class1

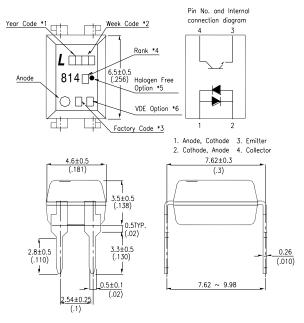
1.2 Applications

- Hybrid substrates that require high density mounting.
- Programmable controllers

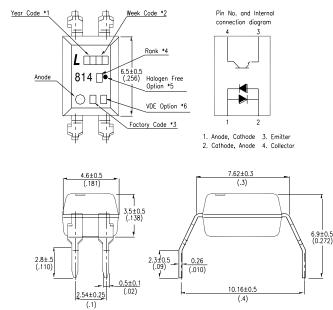


2. PACKAGE DIMENSIONS

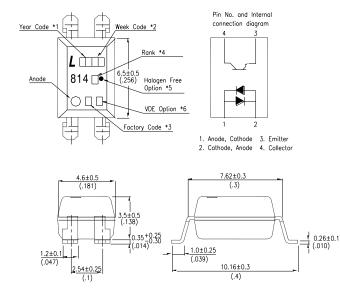
2.1 LTV-814



2.2 LTV-814M



2.3 LTV-814S

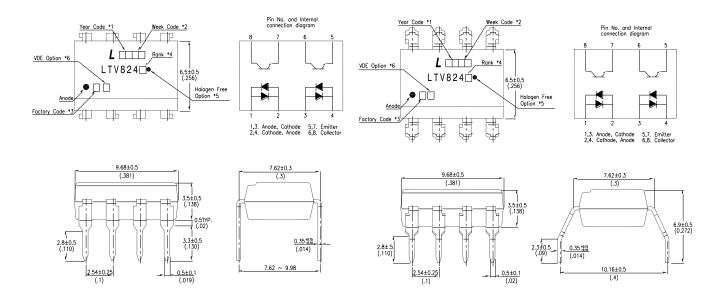


Notes:

- 1. Year date code.
- 2. 2-digit work week.
- 3. Factory identification mark shall be marked (W: China-CZ, Y: Thailand)
- 4. Rank shall be or shall not be marked.
- 5. "●" for halogen free option.
- 6. "4"or"V" for VDE option.

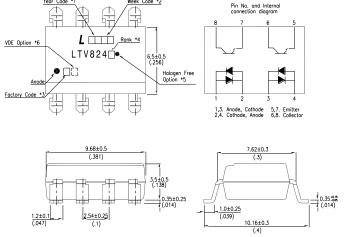


2.4 LTV-824



2.5 LTV-824M

2.6 LTV-824S

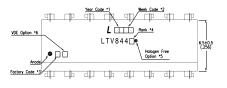


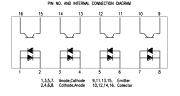
Notes:

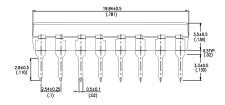
- Year date code.
- 2. 2-digit work week.
- Factory identification mark shall be marked (W: China-CZ, Y: Thailand)
- 4. Rank shall be or shall not be marked.
- "●" for halogen free option.
- 6. "4"or"V" for VDE option.

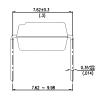


2.7 LTV-844

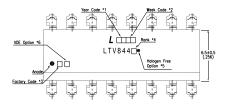


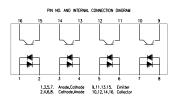


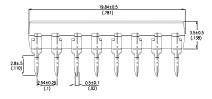


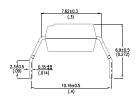


2.8 LTV-844M

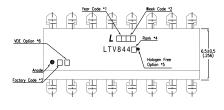


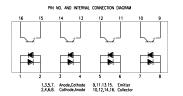


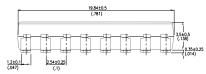


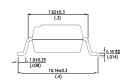


2.9 LTV-844S









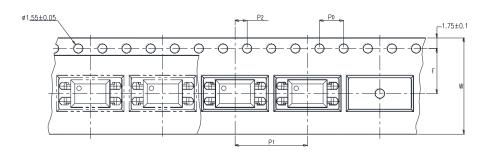
Notes:

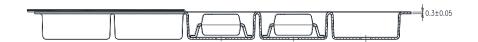
- 1. Year date code.
- 2. 2-digit work week.
- 3. Factory identification mark shall be marked (W: China-CZ, Y: Thailand)
- 4. Rank shall be or shall not be marked.
- "●" for halogen free option.
- 6. "4"or"V" for VDE option.



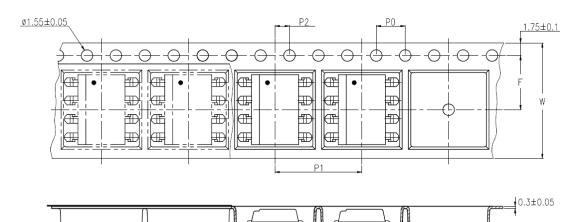
3. TAPING DIMENSIONS

3.1 P/N: LTV-814S-TA1:





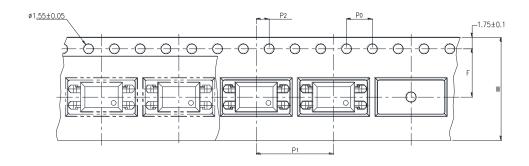
3.2 P/N: LTV-824S-TA1:

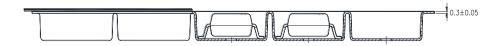


Description	Symbol	Dimension in mm (inch)
Tape wide	W	16±0.3 (0.63)
Pitch of sprocket holes	P ₀	4±0.1 (0.15)
Distance of compartment	F	7.5±0.1 (0.295)
Distance of compartment	P_2	2±0.1 (0.079)
Distance of compartment to compartment	P ₁	12±0.1 (0.472)

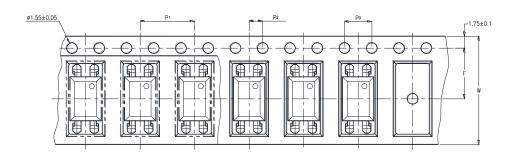


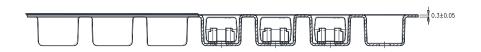
3.2 P/N: LTV-814S-TA:





3.3 P/N: LTV-814S-TP:





Description	Symbol	Dimension in mm (inch)
Tape wide	W	16±0.3 (0.63)
Pitch of sprocket holes	P ₀	4±0.1 (0.15)
Distance of compartment	F	7.5±0.1 (0.295)
Distance of compartment	P ₂	2±0.1 (0.079)
Distance of compartment to compartment	P ₁	12±0.1 (0.472)



4. RATING AND CHARACTERISTICS

4.1 Absolute Maximum Ratings at Ta=25°C

	Parameter	Symbol	Rating	Unit
loout	Forward Current	I _F	±50	mA
Input	Power Dissipation	Р	70	mW
	Collector - Emitter Voltage	V_{CEO}	35	V
Output	Emitter - Collector Voltage	V _{ECO}	6	V
Output	Collector Current	Ic	50	mA
Collector Power Dissipation		Pc	150	mW
	Total Power Dissipation	P _{tot}	200	mW
1.	Isolation Voltage	V _{iso}	5000	V_{rms}
	Operating Temperature (LTV-824/844)	T_{opr}	-30 ~ +100	°C
	Operating Temperature (LTV-814)	T_{opr}	-50 ~ +110	°C
	Storage Temperature	T_{stg}	-55 ~ +125	°C
2	Soldering Temperature	T _{sol}	260	°C

1. AC For 1 Minute, R.H. = 40 ~ 60%

Isolation voltage shall be measured using the following method.

- (1) Short between anode and cathode on the primary side and between collector and emitter on the secondary side.
- (2) The isolation voltage tester with zero-cross circuit shall be used.
- (3) The waveform of applied voltage shall be a sine wave.
- 2. For 10 Seconds



4.2 ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test Condition	
	Forward Voltage	V _F	_	1.2	1.4	V	I _F =±20mA	
Input	Terminal Capacitance	Ct	_	30	250	pF	V=0, f=1KHz	
Output	Collector Dark Current	I _{CEO}	_	_	100	nA	V _{CE} =20V, I _F =0	
	Collector-Emitter Breakdown Voltage	BV _{CEO}	35	_	_	V	I _C =0.1mA, I _F =0	
	Emitter-Collector Breakdown Voltage	BV _{ECO}	6	_	_	V	I _E =10μΑ, I _F =0	
TRANSFER CHARACTERISTICS	Collector Current	Ic	0.2	_	3	mA		
	Current Transfer Ratio	CTR	20	_	300	%	I _F =±1mA, V _{CE} =5V	
	Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	0.1	0.2	V	I _F =±20mA, I _C =1mA	
	Isolation Resistance	R _{iso}	5×10 ¹⁰	1×10 ¹¹	_	Ω	DC500V, 40 ~ 60% R.H.	
	Floating Capacitance	Cf	_	0.6	1	pF	V=0, f=1MHz	
	Cut-off Frequency	f _c	_	80	_	kHz	V_{CE} =5V, I_{C} =2mA R_{L} =100 Ω ,-3dB	
	Response Time (Rise)	tr	_	4	18	μS	V _{CE} =2V, I _C =2mA	
	Response Time (Fall)	tf	_	3	18	μS	R_L =100 Ω ,	

1. CTR =
$$\frac{I_C}{I_F} \times 100\%$$





5. RANK TABLE OF CURRENT TRANSFER RATIO CTR

	CTR Rank	Min	Max	Condition
LTV-814	А	50	160	
	В	100	300	I _F =±1mA V _{CE} =5V
	A or B or No mark	20	300	Ta=25C
LTV-824/844	No mark	20	300	



6. CHARACTERISTICS CURVES

Fig.1 Forword Current vs. Ambient Temperatute

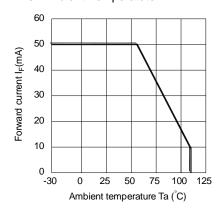


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

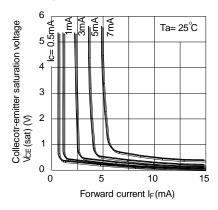


Fig.5 Current Transfer Ratio vs.
Forward Current

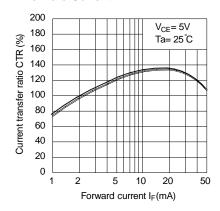


Fig.2 Collector Power Dissiption vs. Ambient Temperature

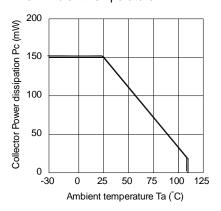


Fig.4 Forward Current vs. Forward Voltage

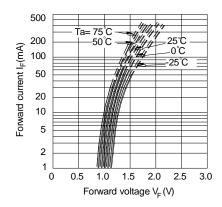
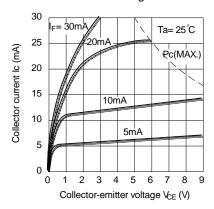


Fig.6 Collector Current vs.

Collector-emitter Voltage



10/15



Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

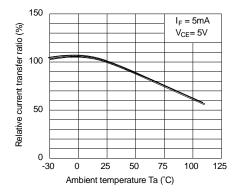


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

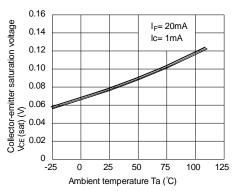


Fig.9 Collector Dark Current vs.
Ambient Temperature

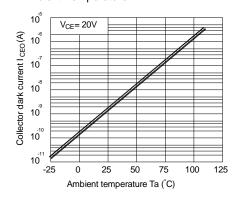


Fig.10 Response Time vs. Load Resistance

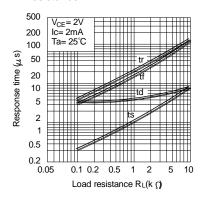
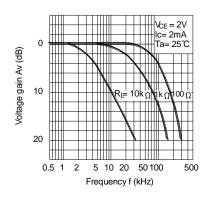
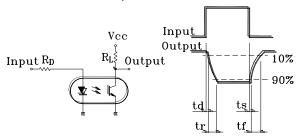


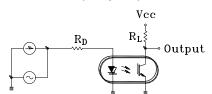
Fig.11 Frequency Response



Test Circuit for Response Time



Test Circuit for Frequency Response



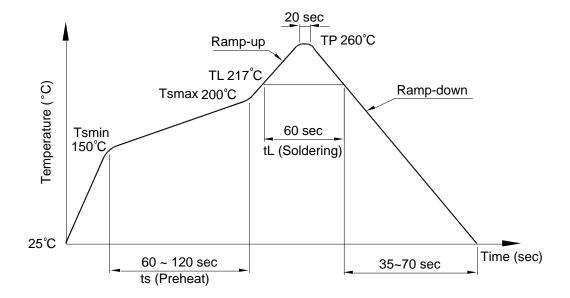


7. TEMPERATURE PROFILE OF SOLDERING

7.1 IR Reflow soldering (JEDEC-STD-020C compliant)

One time soldering reflow is recommended within the condition of temperature and time profile shown below. Do not solder more than three times.

Profile item	Conditions	
Preheat		
- Temperature Min (T _{Smin})	150°C	
- Temperature Max (T _{Smax})	200°C	
- Time (min to max) (ts)	90±30 sec	
Soldering zone		
- Temperature (T _L)	217°C	
- Time (t _L)	60 sec	
Peak Temperature (T _P)	260°C	
Ramp-up rate	3°C / sec max.	
Ramp-down rate	3~6°C / sec	





7.2 Wave soldering (JEDEC22A111 compliant)

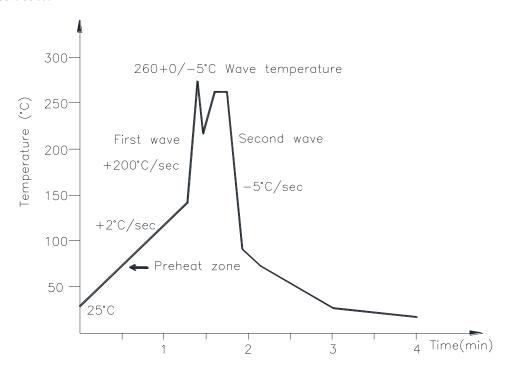
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C

Time: 10 sec.

Preheat temperature:25 to 140°C

Preheat time: 30 to 80 sec.



7.3 Hand soldering by soldering iron

Allow single lead soldering in every single process. One time soldering is recommended.

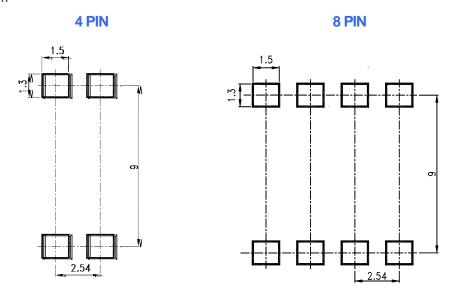
Temperature: 380+0/-5°C

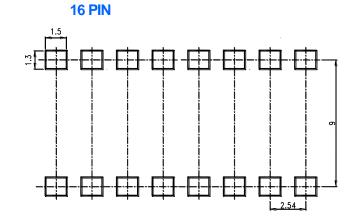
Time: 3 sec max.



8. RRECOMMENDED FOOT PRINT PATTERNS (MOUNT PAD)

Unit: mm









9. Notes:

- LiteOn is continually improving the quality, reliability, function or design and LiteOn reserves the right to make changes without further notices.
- The products shown in this publication are designed for the general use in electronic applications such as office automation equipment, communications devices, audio/visual equipment, electrical application and instrumentation.
- For equipment/devices where high reliability or safety is required, such as space applications, nuclear power control equipment, medical equipment, etc, please contact our sales representatives.
- When requiring a device for any "specific" application, please contact our sales in advice.
- If there are any questions about the contents of this publication, please contact us at your convenience.
- The contents described herein are subject to change without prior notice.
- Immerge unit's body in solder paste is not recommended.